10V Drive Nch MOS FET RDX045N60

Structure

Silicon N-channel MOS FET

● Features

- 1) Low on-resistance.
- 2) Low input capacitance.
- 3) Excellent resistance to damage from static electricity.

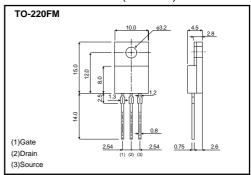
Applications

Switching

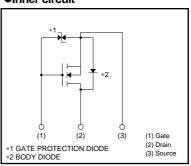
Packaging specifications

	Package	Bulk
Type	Code	_
	Basic ordering unit (pieces)	500
RDX045N60		0

●External dimensions (Unit : mm)



●Inner circuit



●Absolute maximum ratings (Ta=25°C)

Parameter		Symbol		Limits	Unit	
Drain-source voltage		Voss		600	V	
Gate-source voltage		Vgss		±30	V	
Drain augrant	Continuous	ID	*1	±4.5	А	
Drain current	Pulsed	I _{DP}	*2	±18	Α	
Source current (Body diode)	Continuous	ls		4.5	Α	
	Pulsed	I _{SP}	*2	18	Α	
Avalanche current		I _{AS}	*3	4.5	Α	
Avalanche energy		Eas	*4	40	mJ	
Total power dissipation (Tc=25°C)		PD		35	W	
Channel temperature		Tch		150	°C	
Range of storage temperature		Tstg		-55 to +150	°C	

^{*1} Limited only by maximum temperature allowed *3 L \rightleftharpoons 3.4mH VDD=90V Rg=25 Ω *4 L \rightleftharpoons 3.4mH VDD=90V Rg=25 Ω starting Tch=25°C

●Thermal resistance

Parameter	Symbol	Limits	Unit
Channel to case	Rth(ch-c)	3.57	°C/W

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●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Gate-source leakage	Igss	-	_	±10	μΑ	V _{GS} = ±25V, V _{DS} =0V
Drain-source breakdown voltage	V _{(BR) DSS}	600	_	_	V	I _D = 1mA, V _{GS} =0V
Zero gate voltage drain current	IDSS	_	_	25	μΑ	V _{DS} = 600V, V _{GS} =0V
Gate threshold voltage	V _{GS (th)}	2.0	_	4.0	V	V _{DS} = 10V, I _D = 1mA
Static drain-source on-state resistance	R _{DS (on)} *	-	1.6	2.1	Ω	I _D = 2.25A, V _{GS} = 10V
Forward transfer admittance	Y _{fs} *	1.5	2.8	_	S	V _{DS} = 10V, I _D = 2.25A
Input capacitance	Ciss	_	500	_	pF	Vps= 25V
Output capacitance	Coss	_	60	_	pF	Vgs=0V
Reverse transfer capacitance	Crss	-	10	_	pF	f=1MHz
Turn-on delay time	t _{d (on)} *	-	18	_	ns	V _{DD} ≒ 150V
Rise time	tr *	-	16	_	ns	I _D = 2.25A V _G s= 10V
Turn-off delay time	t _{d (off)} *	-	36	_	ns	R _L = 66.7Ω
Fall time	t _f *	-	28	_	ns	R _G =10Ω
Total gate charge	Qg *	_	16	_	nC	V _{DD} ≒300V, V _{GS} =10V
Gate-source charge	Qgs *		4	_	nC	I _D = 4.5A
Gate-drain charge	Q _{gd} *	_	6	_	nC	$R_L=66.7\Omega$, $R_{GS}=10\Omega$

*Pulsed

●Body diode characteristics (Source-drain) (Ta=25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Forward voltage	Vsp *	_	_	1.5	V	I _S = 4.5A, V _{GS} =0V
Reverse recovery time	trr	-	400	_	ns	IDR= 4.5A, VGS=0V
Reverse recovery charge	Qrr	_	4.4	_	μC	di/dt= 100A / μs

^{*}Pulsed

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